

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (original) A method of forming an FSG film, comprising the steps of:

providing a structure; and

forming an FSG film over the structure by an HDP-CVD process under the following conditions:

- a) no Argon (Ar) - side sputter;
- b) an SiF₄ flow: from about 53 to 63 sccm;
- c) an N₂ flow: from about 25 to 35 sccm; and
- d) an RF power to provide a uniform plasma density.

2. (original) The method of claim 1, wherein the structure is comprised of silicon.

3. (original) The method of claim 1, wherein the SiF₄ flow is about 58 sccm and the N₂ flow is about 30 sccm.

4. (canceled)

5. (original) The method of claim 1, wherein the RF power to provide a uniform plasma density includes:

- a) an RF top power of about 1500W;
- b) an RF side power of about 3400W; and
- c) a bias RF power of about 2600 W.

6. (original) The method of claim 1, wherein the FSG film is formed over the structure under the following additional conditions:

- a) an Ar top sputter of from about 4 to 6 sccm;
- b) an SiH₄ flow - side of from about 50 to 56 sccm;
- c) an SiH₄ flow - top of from about 2.8 to 3.2 sccm; and
- d) O₂ flow of from about 133 to 143 sccm.

7. (original) The method of claim 1, wherein the FSG film is formed over the structure under the following additional conditions:

- a) an Ar top sputter of about 5 sccm;
- b) an SiH₄ flow - side of about 53 sccm;
- c) an SiH₄ flow - top of about 3.0 sccm; and
- d) O₂ flow of about 138 sccm.

8. (original) The method of claim 1, wherein the FSG film includes the following characteristics:

- a) a dielectric constant (k) of from about 3.3 to 3.5;
- b) a gap filling ability of from about 0.17 to 0.19 μ m;
- c) a deposition rate of from 4400 to 4800 \AA ; and
- d) a F% of from about 6.80 to 7.40%.

9. (original) The method of claim 1, wherein the formed FSG film includes the following characteristics:

- a) a dielectric constant (k) of about 3.4;
- b) a gap filling ability of about 0.18 μ m;

- c) a deposition rate of from 4600Å; and
- d) a F% of from about 7.10%.

10. (original) The method of claim 1, wherein the formed FSG film has a gap filling ability of from about 0.19 to 0.21µm.

11. (original) The method of claim 1, wherein the formed FSG film has a gap filling ability of from about 0.17 to 0.21µm.

12. (original) The method of claim 1, wherein the formed FSG film includes the following characteristics:

- a) THK U% of from about 1.75 to 1.81%;
- b) WIW range of from about 250 to 350Å;
- c) a D/E of from about 2.65 to 2.71; and
- d) a %F%U of from about 2.3 to 2.7%.

13. (original) The method of claim 1, wherein the formed FSG film 16 includes the following characteristics:

- a) THK U% of from about 1.78%;
- b) WIW range of from about 300Å;
- c) a D/E of from about 2.68; and
- d) a %F%U of from about 2.5%.

14. (original) The method of claim 1, wherein the formed FSG film does not form appreciable Si-OH bonds within about a week of formation.

15. (original) The method of claim 1, wherein the fluorine within the formed FSG film does not appreciably outgas from the formed FSG film.

16. (currently amended) The method of claim 1, including the step of forming at least two adjacent metal ~~structure~~ structures upon the structure before the formation of FSG film.

17. (original) The method of claim 1, including the step of forming at least two adjacent metal structures upon the structure and the FSG film is formed over the at least two adjacent metal structures; wherein the at least two adjacent metal structures include corner and wherein the corners of the at least two adjacent metal structures are not clipped by the deposition of the FSG film.

18. (original) The method of claim 1, including the step of forming at least two adjacent metal structures upon the structure and the FSG film is formed over the at least two adjacent metal structures; wherein the at least two adjacent metal structures include corner and wherein the corners of the at least two adjacent metal structures are not clipped by the deposition of the FSG film; the metal structure being comprised of copper, aluminum or gold.

19. (original) The method of claim 1, including the step of forming at least two adjacent metal structures upon the structure and the FSG film is formed over the at least two adjacent metal structures; wherein the at least two adjacent metal structures include corner and wherein the corners of the at least two adjacent metal structures are not clipped by the deposition of the FSG film; the metal structure being comprised of copper or aluminum.

20. (original) A method of forming an FSG film, comprising the steps of:

providing a structure; and

forming an FSG film over the structure by an HDP-CVD process under the following conditions:

- a) no Argon (Ar) - side sputter;
- b) an SiF₄ flow: from about 53 to 63 sccm;
- c) an N₂ flow: from about 25 to 35 sccm; and
- d) an RF power to provide a uniform plasma density; wherein the RF power to provide a uniform plasma density includes:

- i) an RF top power of from about 1450 to 1550W;
- ii) an RF side power of from about 3300 to 3500W; and
- iii) a bias RF power of from about 2575 to 2625 W.

21. (original) The method of claim 20, wherein the structure is comprised of silicon.

22. (original) The method of claim 20, wherein the SiF₄ flow is about 58 sccm and the N₂ flow is about 30 sccm.

23. (original) The method of claim 20, wherein the RF power to provide a uniform plasma density includes:

- a) an RF top power of about 1500W;
- b) an RF side power of about 3400W; and
- c) a bias RF power of about 2600 W.

24. (original) The method of claim 20, wherein the FSG film is formed over the structure under the following additional conditions:

- a) an Ar top sputter of from about 4 to 6 sccm;
- b) an SiH₄ flow - side of from about 50 to 56 sccm;
- c) an SiH₄ flow - top of from about 2.8 to 3.2 sccm; and
- d) O₂ flow of from about 133 to 143 sccm.

25. (original) The method of claim 20, wherein the FSG film is formed over the structure under the following additional conditions:

- a) an Ar top sputter of about 5 sccm;
- b) an SiH₄ flow - side of about 53 sccm;
- c) an SiH₄ flow - top of about 3.0 sccm; and

- d) O₂ flow of about 138 sccm.

26. (original) The method of claim 20, wherein the FSG film includes the following characteristics:

- a) a dielectric constant (k) of from about 3.3 to 3.5;
- b) a gap filling ability of from about 0.17 to 0.19 μ m;
- c) a deposition rate of from about 4400 to 4800 \AA ; and
- d) a F% of from about 6.80 to 7.40%.

27. (original) The method of claim 20, wherein the formed FSG film includes the following characteristics:

- a) a dielectric constant (k) of about 3.4;
- b) a gap filling ability of about 0.18 μ m;
- c) a deposition rate of about 4600 \AA ; and
- d) a F% of about 7.10%.

28. (original) The method of claim 20, wherein the formed FSG film has a gap filling ability of from about 0.19 to 0.21 μ m.

29. (original) The method of claim 20, wherein the formed FSG film has a gap filling ability of from about 0.17 to 0.21 μ m.

30. (original) The method of claim 20, wherein the formed FSG film includes the following characteristics:

- a) THK U% of from about 1.75 to 1.81 %;
- b) WIW range of from about 250 to 350 \AA ;

- c) a D/E of from about 2.65 to 2.71; and
- d) a %F%U of from about 2.3 to 2.7%.

31. (original) The method of claim 20, wherein the formed FSG film 16 includes the following characteristics:

- a) THK U% of from about 1.78%;
- b) WIW range of from about 300Å;
- c) a D/E of from about 2.68; and
- d) a %F%U of from about 2.5%.

32. (original) The method of claim 20, wherein the formed FSG film does not form appreciable Si-OH bonds within about a week of formation.

33. (original) The method of claim 20, wherein the fluorine within the formed FSG film does not appreciably outgas from the formed FSG film.

34. (currently amended) The method of claim 20, including the step of forming at least two adjacent metal ~~structure~~ structures upon the structure before the formation of FSG film.

35. (currently amended) The method of claim 20, including the step of forming at least two adjacent metal structures upon the structure and the FSG film is formed over the at least two adjacent metal structures; wherein the at least two adjacent metal structures include ~~corner~~ corners and wherein the corners of the at least two adjacent metal structures are not clipped by the deposition of the FSG film.

36. (currently amended) The method of claim 20, including the step of forming at least two adjacent metal structures upon the structure and the FSG film is formed over the at least two adjacent metal structures; wherein the at least two adjacent metal structures include ~~corner~~ corners and wherein the corners of the at least two adjacent metal structures are not clipped by

the deposition of the FSG film; the metal structure being comprised of copper, aluminum or gold.

37. (currently amended) The method of claim 20, including the step of forming at least two adjacent metal structures upon the structure and the FSG film is formed over the at least two adjacent metal structures; wherein the at least two adjacent metal structures include ~~corner~~ corners and wherein the corners of the at least two adjacent metal structures are not clipped by the deposition of the FSG film; the metal structure being comprised of copper or aluminum.

38. (original) A method of forming an FSG film, comprising the steps of:

providing a structure; and

forming an FSG film over the structure by an HDP-CVD process under the following conditions:

- a) no Argon (Ar) - side sputter;
- b) an SiF₄ flow: about 58 sccm;
- c) an N₂ flow: about 30 sccm; and
- d) an RF power to provide a uniform plasma density; wherein the RF power to provide a uniform plasma density includes:
 - i) an RF top power of about 1500W;
 - ii) an RF side power of about 3400W; and
 - iii) a bias RF power of about 2600 W.

39. (original) The method of claim 38, wherein the structure is comprised of silicon.

40. (original) The method of claim 38, wherein the FSG film is formed over the structure under the following additional conditions:

- a) an Ar top sputter of from about 4 to 6 sccm;
- b) an SiH₄ flow - side of from about 50 to 56 sccm;

- c) an SiH₄ flow - top of from about 2.8 to 3.2 sccm; and
- d) O₂ flow of from about 133 to 143 sccm.

41. (original) The method of claim 38, wherein the FSG mm is formed over the structure under the following additional conditions:

- a) an Ar top sputter of about 5 sccm;
- b) an SiH₄ flow - side of about 53 sccm;
- c) an SiH₄ flow - top of about 3.0 sccm; and
- d) O₂ flow of about 138 sccm.

42. (original) The method of claim 38, wherein the FSG film includes the following characteristics:

- a) a dielectric constant (k) of from about 3.3 to 3.5;
- b) a gap filling ability of from about 0.17 to 0.19 μ m;
- c) a deposition rate of from about 4400 to 4800 \AA ; and
- d) a F% of from about 6.80 to 7.40%.

43. (original) The method of claim 38, wherein the formed FSG film includes the following characteristics:

- a) a dielectric constant (k) of about 3.4;
- b) a gap filling ability of about 0.18 μ m;
- c) a deposition rate of about 4600 \AA ; and
- d) a F% of about 7.10%.

44. (original) The method of claim 38, wherein the formed FSG film has a gap filling ability of from about 0.19 to 0.21 μm .

45. (original) The method of claim 38, wherein the formed FSG film has a gap filling ability of from about 0.17 to 0.21 μm .

46. (original) The method of claim 38, wherein the formed FSG film includes the following characteristics:

- a) THK U% of from about 1.75 to 1.81%;
- b) WIW range of from about 250 to 350 \AA ;
- c) a D/E of from about 2.65 to 2.71; and
- d) a %F%U of from about 2.3 to 2.7%.

47. (original) The method of claim 38, wherein the formed FSG film 16 includes the following characteristics:

- a) THK U% of from about 1.78%;
- b) WIW range of from about 300 \AA ;
- c) a D/E of from about 2.68; and
- d) a %F%U of from about 2.5%.

48. (original) The method of claim 38, wherein the formed FSG film does not form appreciable Si-OH bonds within about a week of formation.

49. (original) The method of claim 38, wherein the fluorine within the formed FSG film does not appreciably outgas from the formed FSG film.

50. (currently amended) The method of claim 38, including the step of forming at least two adjacent metal ~~structure~~ structures upon the structure before the formation of FSG film.

51. (currently amended) The method of claim 38, including the step of forming at least two adjacent metal structures upon the structure and the FSG film is formed over the at least two adjacent metal structures; wherein the at least two adjacent metal structures include ~~corner~~ corners and wherein the corners of the at least two adjacent metal structures are not clipped by the deposition of the FSG film.

52. (currently amended) The method of claim 38, including the step of forming at least two adjacent metal structures upon the structure and the FSG film is formed over the at least two adjacent metal structures; wherein the at least two adjacent metal structures include ~~corner~~ corners and wherein the corners of the at least two adjacent metal structures are not clipped by the deposition of the FSG film; the metal structure being comprised of copper, aluminum or gold.

53. (currently amended) The method of claim 38, including the step of forming at least two adjacent metal structures upon the structure and the FSG film is formed over the at least two adjacent metal structures; wherein the at least two adjacent metal structures include ~~corner~~ corners and wherein the corners of the at least two adjacent metal structures are not clipped by the deposition of the FSG film; the metal structure being comprised of copper or aluminum.